

FORM PT 01449 (Modified)	ATTY. DOCKET NO. FIS9-2003-0235US1	SERIAL NO. 10/707,841
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT: Haining S. Yang, et al.	
(Use several sheets if necessary)	FILING DATE: 01/16/2004	GROUP: Unassigned 2813

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	6,228,694 B1	5/8/2001	Doyle et al.			
	6,406,973 B1	6/18/2002	Lee			
	6,281,532 B1	8/28/2001	Doyle et al.			
	5,683,934	11/4/97	Candelaria			
	6,368,931 B1	4/9/2002	Kuhn, et al.			
	5,310,446	5/10/94	Konishi et al.			
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	US 2002/0090791 A1	7/11/2002	Doyle et al.			
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	6,509,618 B2	01/21/2003	Jan et al.			
	6,476,462 B2	11/5/2002	Shimizu et al.			
/JC/	6,362,082 B1	3/26/2002	Doyle et al.			
/JC/	5,565,697	10/15/96	Asakawa et al.			
	US 2003/0040158 A1	2/27/2003	Saitoh			
	US 2002/0086472 A1	7/4/2002	Roberds et al.			
	6,521,964 B1	2/18/2003	Jan et al.			
/JC/	6,506,652	01/14/03	Jan, et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

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EXAMINER /Jack Chen/ (02/04/2008)	DATE CONSIDERED 02/04/2008
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/JC/	5,081,513	1/14/1992	Jackson, et al.			
	3,602,841	8/31/1971	McGroddy			
	6,531,740	3/11/2003	Bosco, et al.			
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	6,493,497	12/10/2002	Ramdani, et al.			
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	6,361,885	3/26/2002	Chou			
	6,255,169	7/3/2001	Li, et al.			
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	6,133,071	10/17/2000	Nagai			
	6,046,464	4/4/2000	Schetzina			
/JC/	6,025,280	2/15/2000	Brady, et al.			

FOREIGN PATENT DOCUMENTS

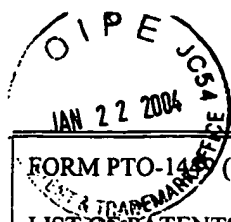
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EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,940,736	8/17/1999	Brady, et al.			
	5,880,040	3/9/1999	Sun, et al.			
	5,861,651	1/19/1999	Brasen, et al.			
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	5,561,302	10/1/1996	Candelaria			
	5,471,948	12/5/1995	Burroughes, et al.			
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	5,060,030	10/22/1991	Hoke			
	4,958,213	9/18/1990	Eklund, et al.			
/JC/	4,665,415	5/12/1987	Esaki, et al.			

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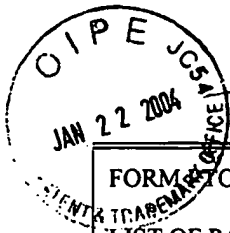
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,989,978	11/23/1999	Peidous			
	6,284,626	9/4/2001	Kim			
	6,274,444	8/14/2001	Wang			
	6,261,964	7/17/2001	Wu, et al.			
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	6,107,143	8/22/2000	Park, et al.			
	6,090,684	7/18/2000	Ishitsuka, et al.			
	6,066,545	5/23/2000	Doshi, et al.			
	6,008,126	12/28/1999	Leedy			
	5,946,559	8/31/1999	Leedy			
	5,840,593	11/24/1998	Leedy			
	5,592,018	1/7/1997	Leedy			
	5,592,007	1/7/1997	Leedy			
/JC/	5,571,741	11/5/1996	Leedy			

FOREIGN PATENT DOCUMENTS

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ATTY. DOCKET NO.
FIS9-2003-0235US1SERIAL NO.
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STATEMENTAPPLICANT:
Haining S. Yang, et al.

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Unassigned 2813

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
/JC/	5,557,122	9/17/1996	Shrivastava, et al.			
	5,354,695	10/11/1994	Leedy			
	5,134,085	7/28/1992	Gilgen, et al.			
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	4,952,524	8/28/1990	Lee, et al.			
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	5,960,297	09-28-1999	Saki			
	6,403,486	06-11-2002	Lou			
	6,284,623	09-04-2001	Zhang et al.			
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	2003/0067035	04-10-2003	Tews et al.			
	6,461,936	10-08-2002	von Ehrenwall			
	6,319,794	11-20-2001	Akatsu et al.			
/JC/	2001/0009784	07-26-2001	Ma et al.			

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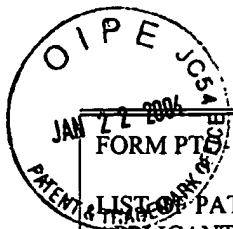
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Unassigned 813

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

/JC/		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si <i>n</i> -MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
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/JC/		K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27160		Application No. 10/707,841	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Haining S. YANG			
				Filing Date January 16, 2004		Group 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/JC/		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
		US 2003/0040158 A1	2-27-2003	Saitoh			
		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
		US 2004/0262784 A1	12-30-2004	Doris et al.			
		US 2005/0040460 A1	2-24-2005	Chidambarao et al.			
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		US 2006/0057787 A1	3-16-2006	Doris et al.			
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		6,825,529	11-30-2004	Chidambarao et al.			
		7,015,082	3-21-2006	Doris et al.			
		6,974,981	12-13-2005	Chidambarao et al.			
/JC/		6,977,194	12-20-2005	Belyansky et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
/JC/		JP 64-76755	3-22-1989	Japan			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
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FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27160		Application No. 10/707,841	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Haining S. YANG			
				Filing Date January 16, 2004		Group 2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
/JC/		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
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		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.					
		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.					
		Subramanian S. Iyer, et al. " Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064					
		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050					
		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462					
/JC/		Q. Quyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000, IEEE, pp. 151-154.					
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